

GSMDS6808

60V Dual N-Channel MOSFETs

Product Description

These Dual N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are well suited for high efficiency fast switching applications.


Features

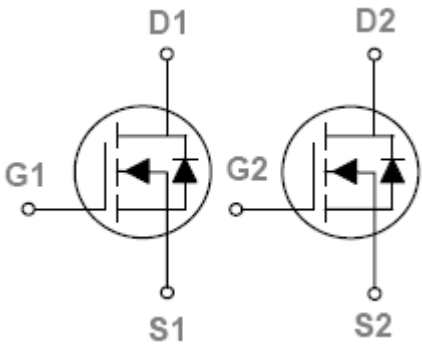
- 60V, 10A, $R_{DS(ON)}=34m\Omega@V_{GS}=10V$
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available
- SOP-8 package design

Applications

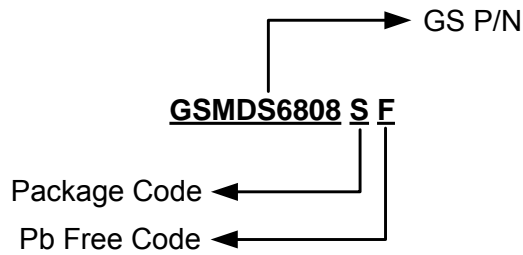
- Motor Drive
- Power Tools
- LED Lighting

Packages & Pin Assignments

GSMDS6808SF (SOP-8)	
 <p style="text-align: center;">Top View</p>	
Pin	Description
1	Source 1
2	Gate 1
3	Source 2
4	Gate 2
5	Drain 2
6	Drain 2
7	Drain 1
8	Drain 1

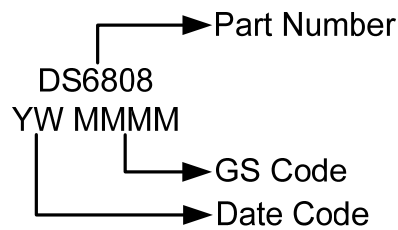


Ordering Information



Part Number	Package	Quantity Reel
GSMDS6808SF	SOP-8	3000 PCS

Marking Information



Absolute Maximum Ratings

T_A=25°C Unless otherwise noted

Symbol	Parameter	Typical	Unit
V _{DS}	Drain-Source Voltage	60	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Continuous Drain Current	T _A =25°C	10
		T _A =100°C	6.3
I _{DM}	Pulsed Drain Current	40	A
EAS	Single Pulse Avalanche Energy	24	mJ
IAS	Single Pulse Avalanche Current	22	A
P _D	Power Dissipation (T _A =25°C)	2.1	W
	Power Dissipation (Derate above 25°C)	0.017	W/°C
T _J	Operating Junction Temperature Range	-50 to +150	°C
T _{STG}	Storage Temperature Range	-50 to +150	°C
R _{θJA}	Thermal Resistance-Junction to Ambient	60	°C/W

Electrical Characteristics

T_A=25°C Unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	60			V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA		0.07		V/°C
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1.2	1.8	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient			-4.6		mV/°C
I _{GSS}	Gate Leakage Current	V _{DS} =0V, V _{GS} =±20V			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V			1	uA
		V _{DS} =48V, V _{GS} =0V, T _J =125°C			10	
I _S	Continuous Source Current	V _G =V _D =0V, Force Current			10	A
I _{SM}	Pulsed Source Current				40	
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V, I _D =10A		28	34	mΩ
		V _{GS} =4.5V, I _D =6A		34	44	
g _{FS}	Forward Transconductance	V _{DS} =10V, I _D =10A		6		S
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =1A			1	V
t _{rr}	Reverse Recovery Time	V _{GS} =0V, I _S =1A, di/dt=100A/us		14	28	ns
Q _{rr}	Reverse Recovery Charge			10	20	
Dynamic						
Q _g	Total Gate Charge	V _{DS} =30V, V _{GS} =10V, I _D =10A		16.6	24	nC
Q _{gs}	Gate-Source Charge			2.2	4.4	
Q _{gd}	Gate-Drain Charge			3.9	8	
C _{iss}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, f=1MHz		1180	1720	pF
C _{oss}	Output Capacitance			68	100	
C _{rss}	Reverse Transfer Capacitance			45	70	
t _{d(on)}	Turn-On Time	V _{DD} =30V, I _D =1A, V _{GS} =10V, R _G =6Ω		4.6	9	ns
t _r				14.8	28	
t _{d(off)}	Turn-Off Time			27.2	52	
t _f				7.8	15	
R _g	Gate Resistance		V _{DS} =0V, V _{GS} =0V, f=1MHz		2.1	

Typical Performance Characteristics

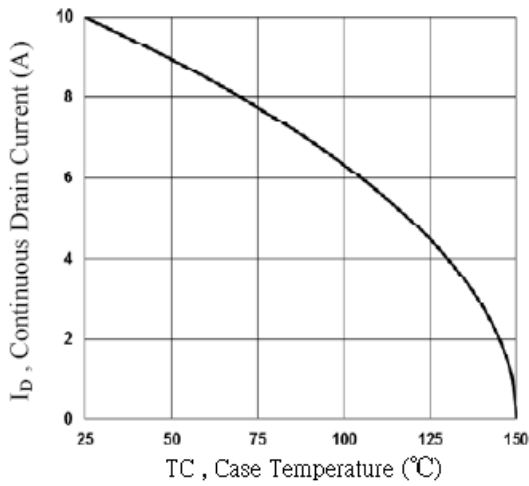


Fig.1 Continuous Drain Current vs. T_c

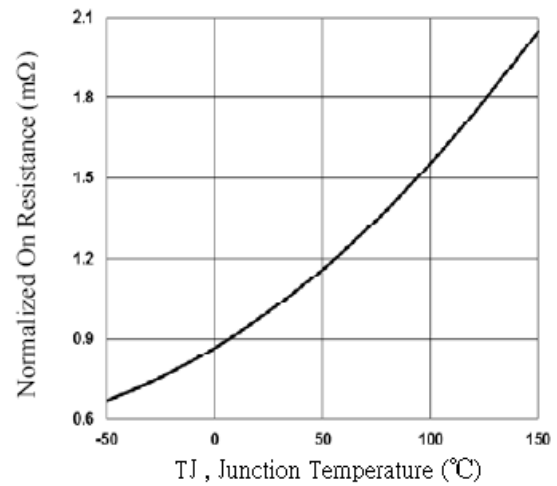


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

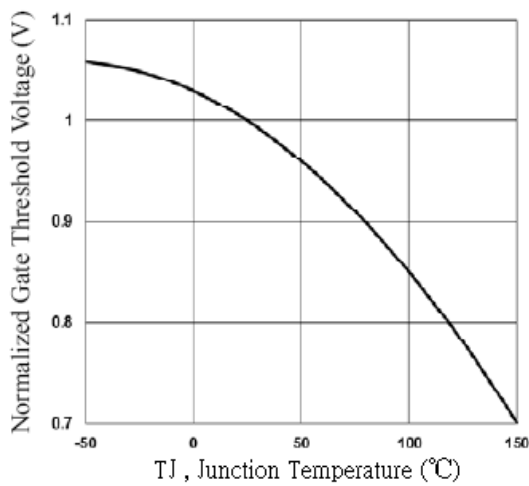


Fig.3 Normalized V_{th} vs. T_j

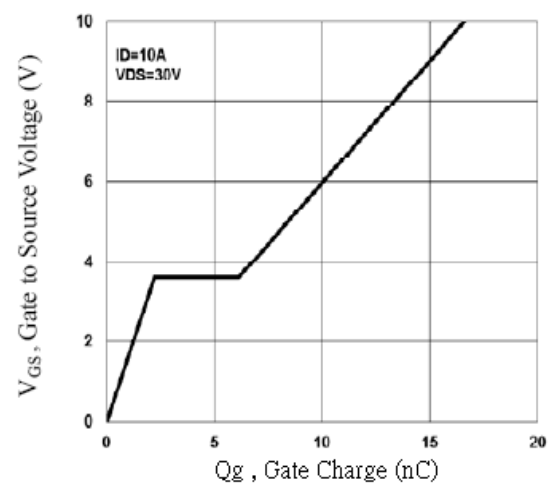


Fig.4 Gate Charge Waveform

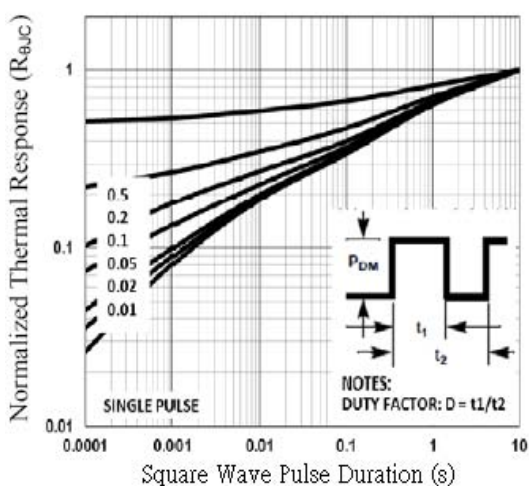


Fig.5 Normalized Transient Impedance

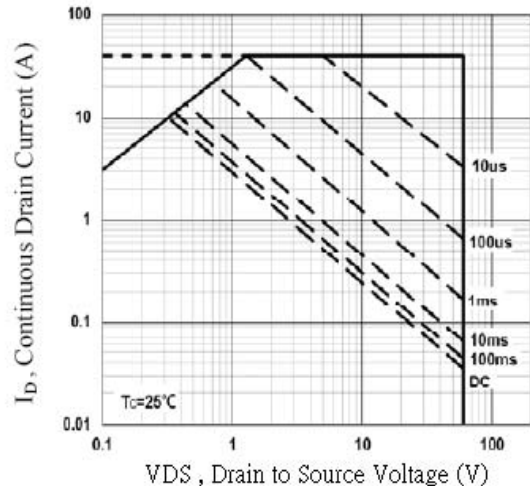
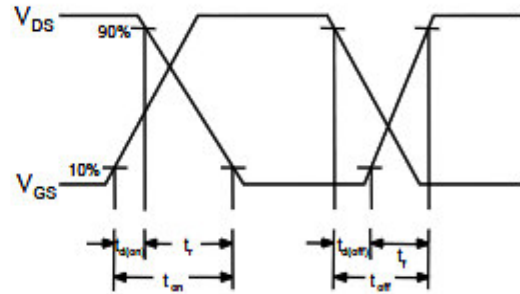
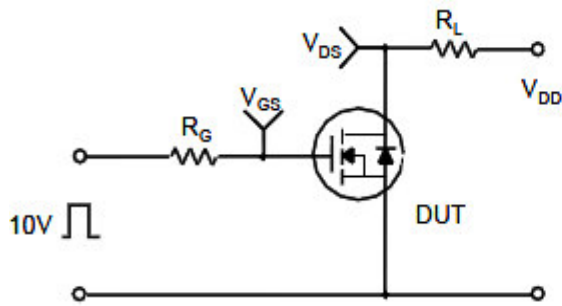


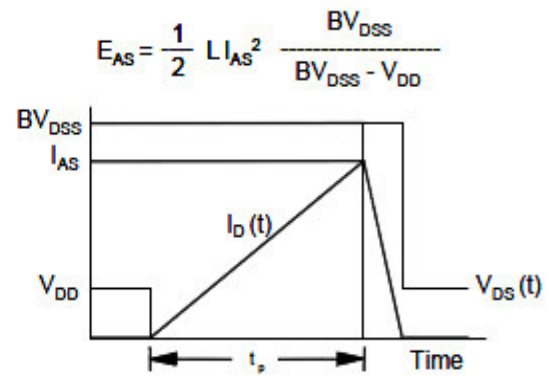
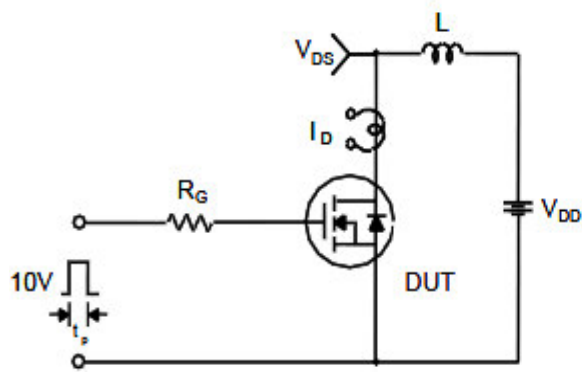
Fig.6 Maximum Safe Operation Area

Typical Performance Characteristics (Continue)

Resistive Switching Test Circuit & Waveforms

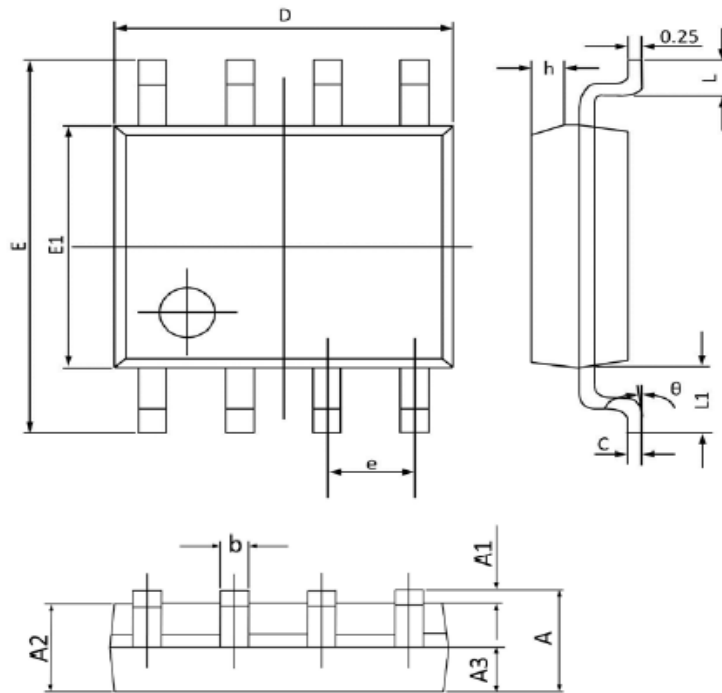


Unclamped Inductive Switching Test Circuit & Waveforms



Package Dimension

SOP-8










Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.068
A1	0.100	0.250	0.004	0.009
A2	1.300	1.500	0.052	0.059
A3	0.600	0.700	0.024	0.027
b	0.390	0.480	0.016	0.018
c	0.210	0.260	0.009	0.010
D	4.700	5.100	0.186	0.200
E	5.800	6.200	0.229	0.244
E1	3.700	4.100	0.146	0.161
e	1.270 (BSC)		0.050 (BSC)	
h	0.250	0.500	0.010	0.019
L	0.500	0.800	0.019	0.031
L1	1.050 (BSC)		0.041 (BSC)	
θ	0°	8°	0°	8°



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CONTACT US

GS Headquarter	
	4F.,No.43-1,Lane11,Sec.6,Minquan E.Rd Neihu District Taipei City 114, Taiwan (R.O.C)
	886-2-2657-9980
	886-2-2657-3630
	sales_twn@gs-power.com

Shenzhen Branch(China)	
	1113 B Building, Happiness Washington, Baoan Nan Road, Luohu District, Shenzhen City, China
	0755-22208941
	sales_cn@gs-power.com

RD Division	
	824 Bolton Drive Milpitas. CA. 95035
	1-408-457-0587